



Silicon Carbide: a game changer in power electronics

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Agenda

Power electronics is increasingly the driver of our future world

Key role of power conversion efficiency

The central role of silicon carbide

Market demand and ST strategy

Focus on ST SiC technology

Takeaways

From combustion to conversion



Efficiency and optimized power transfer

High efficiency technologies are required to reduce losses at all stages of energy flow, from production to consumption

Generation

**Transmission &
distribution**





Storage & conversion

Consumption



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Megatrends driving adoption of SiC

What?	 Electric vehicle	 Charging station	 Renewables	 Power supplies
Where?	<ul style="list-style-type: none">• Onboard chargers• DC-DC converters• Traction inverters• Other – PTC heater, e-compressor, etc.	<ul style="list-style-type: none">• Industrial chargers• EV DC fast chargers• EV wireless chargers	<ul style="list-style-type: none">• Solar inverters• Energy storage systems• Wind power	<ul style="list-style-type: none">• AC/DC server power supplies• Telecom AC-DC rectifiers• UPS
Why?	Small size & weight, high efficiency, longer driving range	High efficiency, low cost, ease of thermal management	High efficiency, low system cost	High efficiency, high power density, lower energy costs

ST SiC MOSFET focus applications and prospects

Focus applications



Power supply



UPS



Solar Inverter



Industrial Motors



EV Charger



Traction



OBC,
DC-DC

ST business prospects

>50%*

2022 Market share automotive & industrial

~\$1.14B

SiC revenues in 2023



>155

projects in development



More than 25 years of focus on SiC at ST

Catania: Power Electronics Competence Center

Ecosystem made of Academic, Research Centers and ST as a semiconductor leader, created a true “incubator”



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Consiglio Nazionale Ricerche

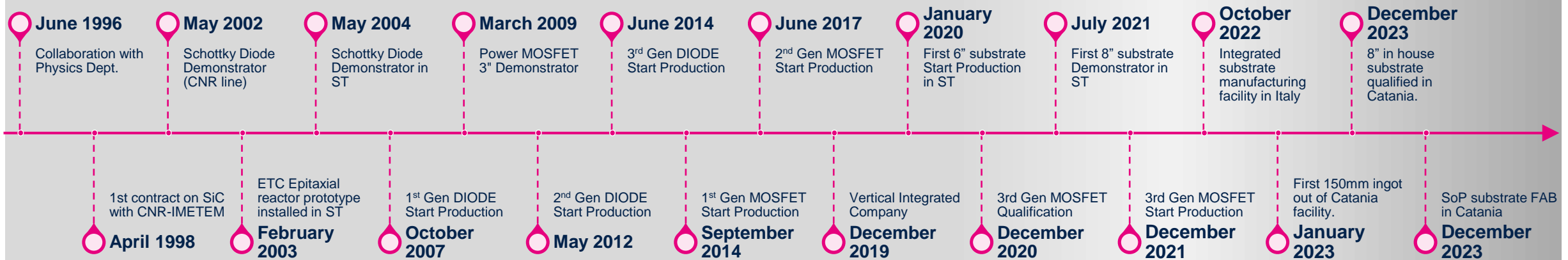
Everything started from 1-inch wafer

More than 110 patents and 650 technical documents

Leveraging on CNR on-site facilities at early stage

> 30 years of experience in power semiconductor

ST major milestones:





Vertically integrating for supply chain robustness

Improving process control and efficiency, from powder to final product

Raw material → SiC ingots & substrates → SiC dice manufacturing → design & manufacture → products

Norrköping SiC substrate R&D plant



- 150 mm production
- 200 mm with industrial quality and yields

Catania new integrated SiC plant



- Pilot production started in 2023*
- 150 mm substrates + epitaxy (converting to 200 mm)

* targeting > 40% substrate in-sourcing by 2024

Silicon carbide substrate manufacturing facility in Italy



Increasing demand for SiC devices across automotive and industrial applications

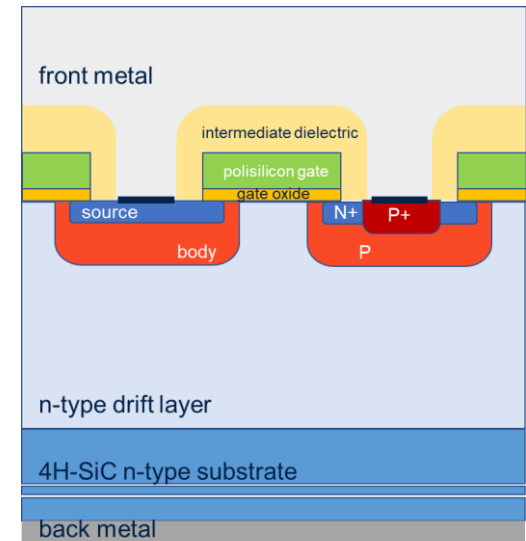
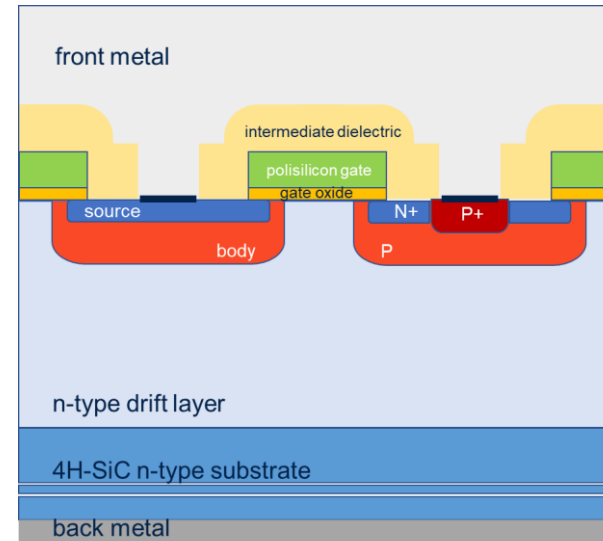
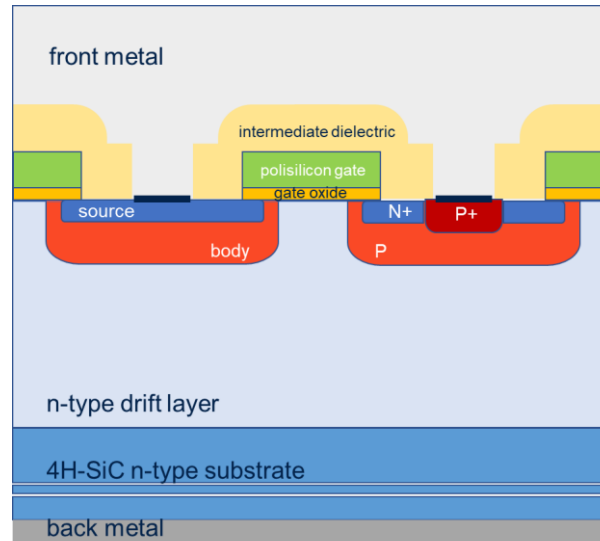
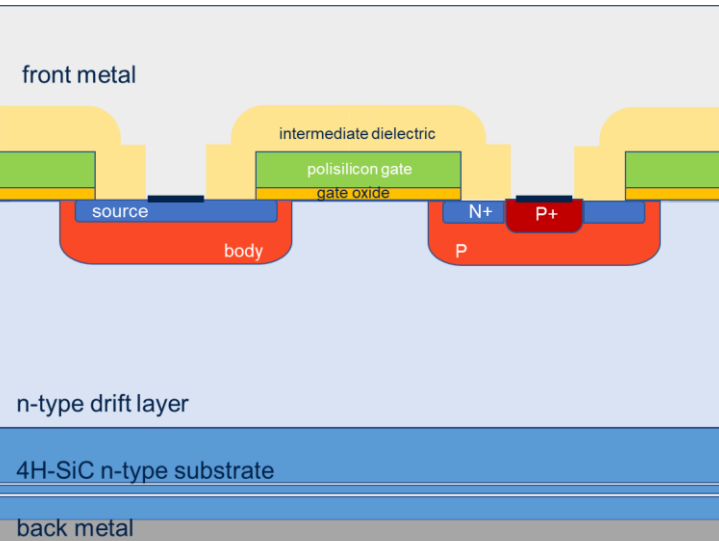
A new integrated **silicon carbide (SiC)** substrate manufacturing **facility** in Italy

Unique in Europe to produce **150mm** SiC epitaxial substrates – to become **200mm** wafer in the near future

Volume production is expected to start in **2024**

700 additional jobs

SiC planar MOSFET technology evolution



Gen2



Gen3



Gen4



Gen5

same contact
same channel
reduced jfet
same edge
improved epi

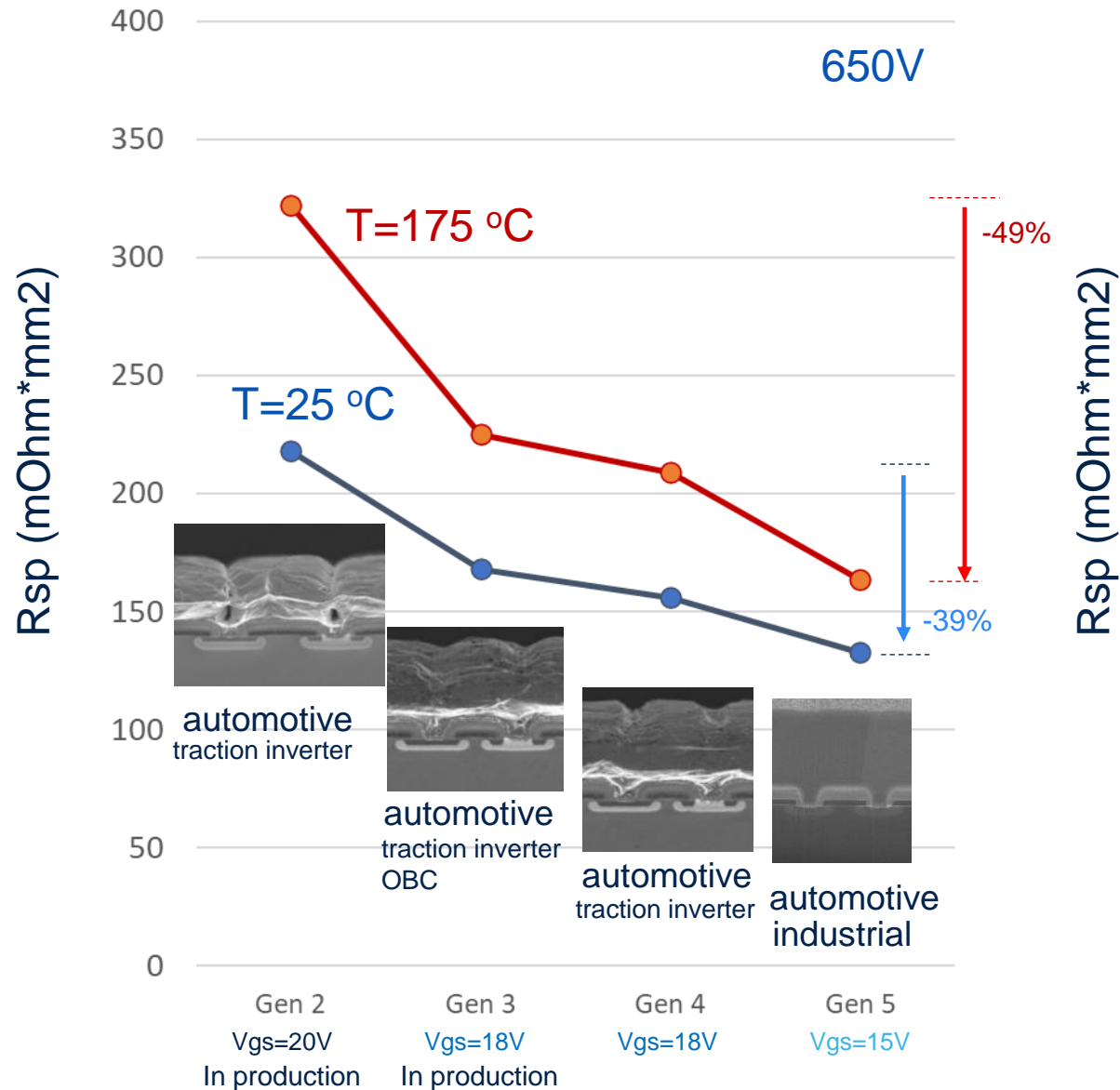
same contact
same channel
same jfet
optimized egde
improved epi

reduced contact dimension
same channel
same jfet
same egde
same epi

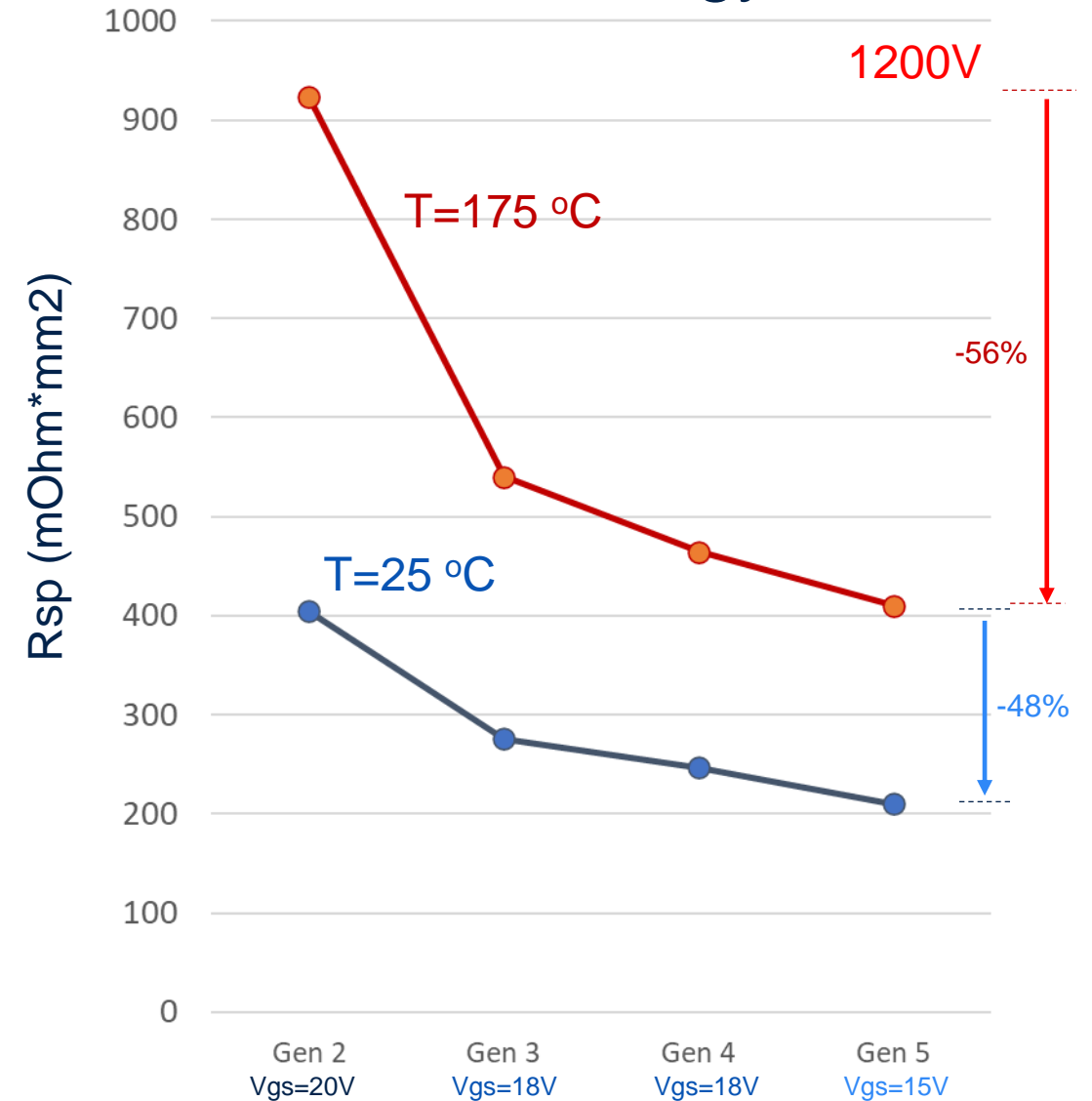
same channel

Designed in SiCily

experimental data

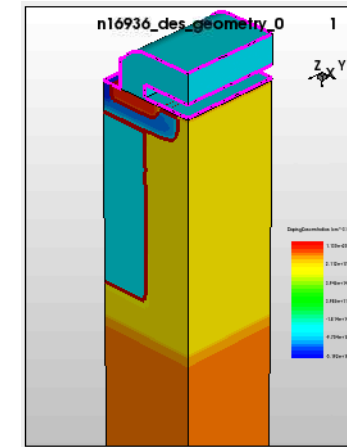
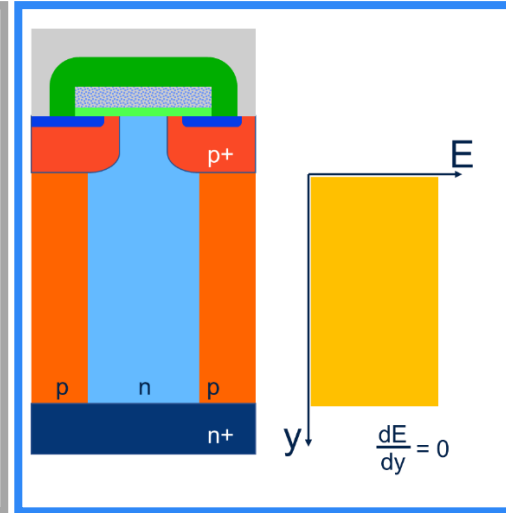
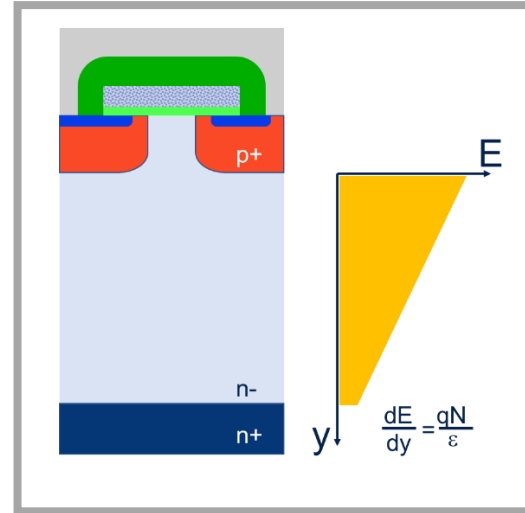
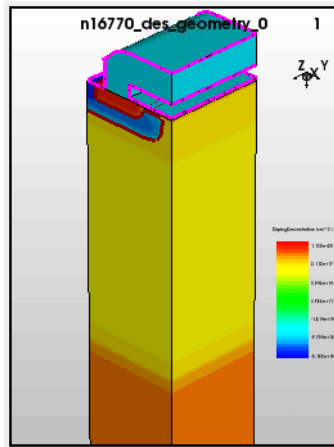


SiC Planar MOSFET technology evolution

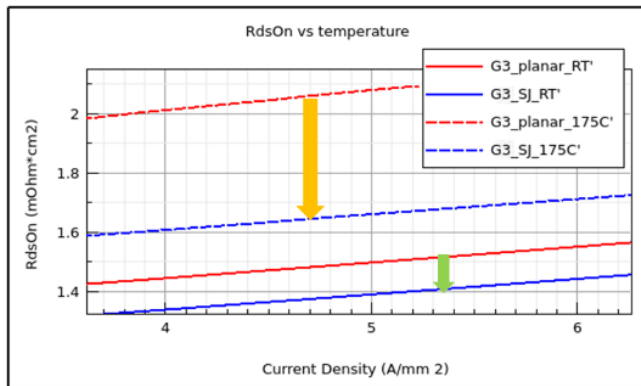


next? Superjunction advantage

Planar vs. Superjunction



Charge balanced drain



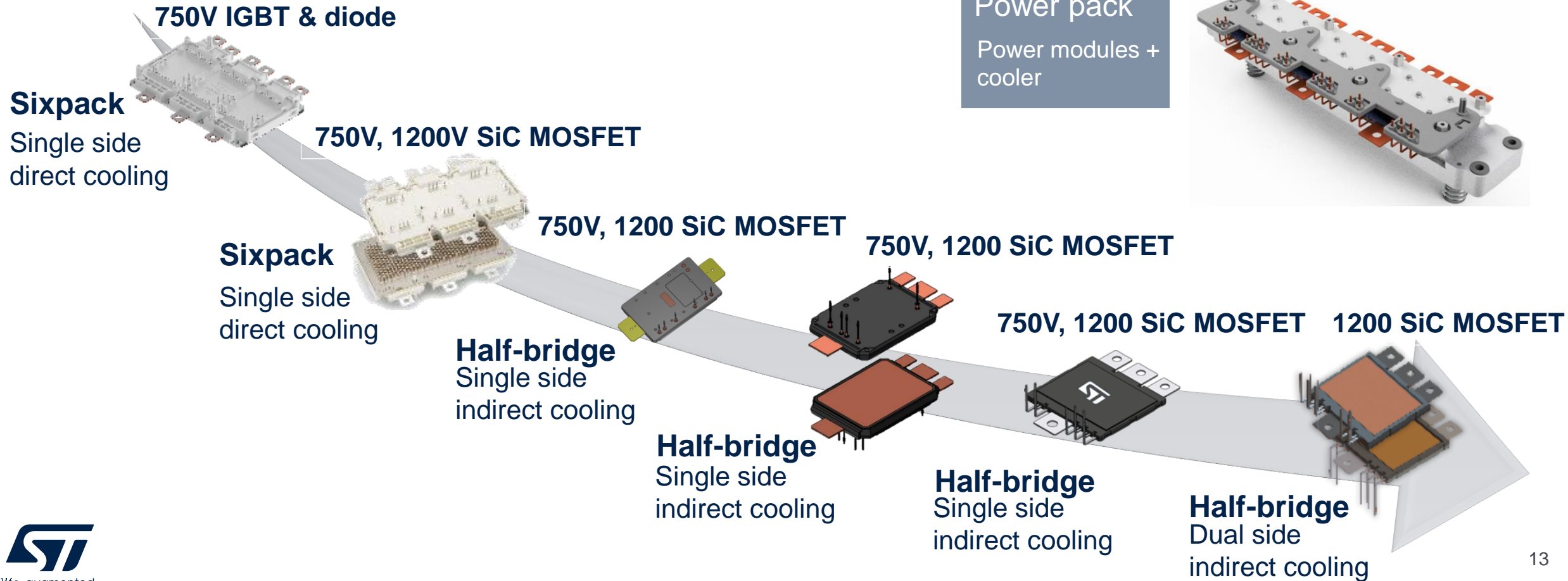
IV simulation

	RT	175°C
650V	- 7%	- 20%
1200V	- 34%	- 59%

Comparison done with same planar structure

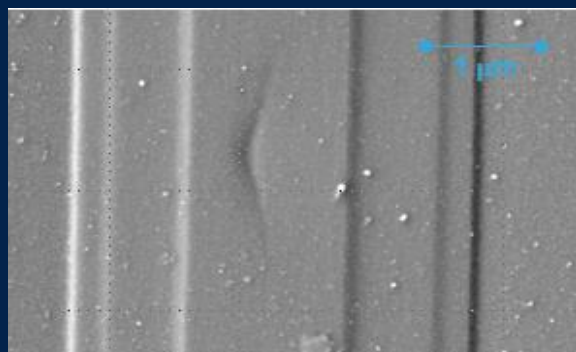
Innovation trend power package technology evolution

Power module evolution towards discrete molded packages



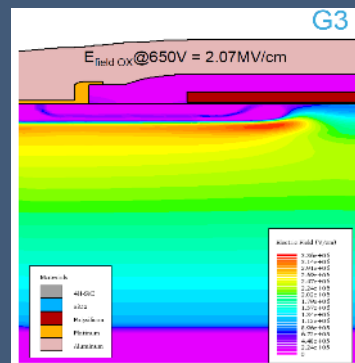
Four vectors for WBG deployment and validation

Failure analyses



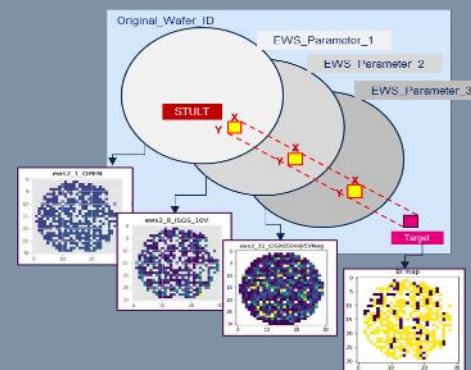
- Identification of new failure modes
- Effectiveness evaluation of screening methods
- Support for customer use in application
- New FA techniques

Design improvement



- Design fine tunings based on new failure mode
- Design for reliability and more margin
- Front-end & back-end new material and design solution evaluation

Testing improvement



- Fine tuning of testing in EWS and back-end
- Burn in testing for new technologies
- DOLI implementation for known defects

Mission profile assessment



- Analysis of customer specific mission profile
- Fine tuning of testing and reliability assessment
- Equivalent FIT evaluation

Takeaways



Silicon carbide plays a key role in **power conversion efficiency**

Demand for SiC is growing fast to support the electrification of the automotive and industrial markets

ST is investing to support the market needs with a **vertical integration** manufacturing strategy

ST offers a wide range of **package solutions** according to customer needs

ST Planar SiC MOSFET technology is **state-of-the-art and best positioned** to support the growth today

Our technology starts with You



Find out more at www.st.com/stpower

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